

NTE384 Silicon NPN Transistor High Voltage Power Amp/Switch

Description:

The NTE384 is a multiple epitaxial silicon NPN power transistor in a TO66 type package utilizing a multiple-emitter site structure. Multiple-epitaxial construction maximizes the volt-ampere characteristic of the device and provides fast switching speeds. Multiple-emitter design ensures uniform current flow throughout the structure, which produces a high $I_{S/b}$ and a large safe-operation-area.

The NTE384 is characterized for use in inverters operating directly from a rectified 110V power line. The leakage current is specified at 450V; therefore the device can also be used in a series bridge configuration on a 220V line. The V_{EBO} rating of 9V eases requirements on the drive transformer in inverter applications.

Features:

- Maximum Safe-Area-of-Operation
- Low Saturation Voltages
- High Voltage Rating: $V_{CER(sus)} = 375V$
- High Dissipation Rating: $P_T = 45W$

Absolute Maximum Ratings:

Collector-Base Voltage, V_{CBO}	375V
Collector-Emitter Sustaining Voltage	
With Base Open, $V_{CEO(sus)}$	350V
With Reverse Bias (V_{BE}) of $-1.5V$, $V_{CEX(sus)}$	375V
With External Base-Emitter Resistance (R_{BE}) $\leq 50\Omega$, $V_{CER(sus)}$	375V
Emitter-Base Voltage, V_{EBO}	9V
Collector Current, I_C	
Continuous	7A
Peak	10A
Continuous Base Current, I_B	4A
Transistor Dissipation ($T_C \leq +25^\circ C$, $V_{CE} \leq 40V$), P_T	45W
Operating Junction Temperature Range, T_{opr}	-65° to $+200^\circ C$
Storage Temperature Range, T_{stg}	-65° to $+200^\circ C$
Lead Temperature (During Soldering, 1/32 in. (0.8mm) from case, 10sec max), T_L	$+230^\circ C$
Thermal Resistance, Junction to Case ($V_{CE} = 20V$, $I_C = 2.25A$), $R_{\theta JC}$	$3.9^\circ C/W$

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Cutoff Current	I_{CEV}	$V_{CE} = 450\text{V}$, $V_{BE} = -1.5\text{V}$	–	–	0.5	mA
		$V_{CE} = 450\text{V}$, $V_{BE} = -1.5\text{V}$, $T_C = +125^\circ\text{C}$	–	–	5.0	mA
Emitter–Cutoff Current	I_{EBO}	$V_{BE} = -9\text{V}$, $I_C = 0$	–	–	1.0	mA
Collector–Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 200\text{mA}$, Note 1, Note 2	350	–	–	V
	$V_{CER(sus)}$	$I_C = 200\text{mA}$, $R_{BE} = 50\Omega$, Note 1, Note 2	375	–	–	V
Emitter–Base Voltage	V_{EBO}	$I_C = 0$	9	–	–	V
DC Forward Current	h_{FE}	$V_{CE} = 1\text{V}$, $I_C = 1.2\text{A}$, Note 1	12	28	50	
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 1.2\text{A}$, $I_B = 200\text{mA}$, Note 1	–	1.0	1.6	V
		$I_C = 4\text{A}$, $I_B = 800\text{mA}$, Note 1	–	1.3	2.0	V
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1.2\text{A}$, $I_B = 200\text{mA}$, Note 1	–	0.15	0.5	V
		$I_C = 4\text{A}$, $I_B = 800\text{mA}$, Note 1	–	0.5	3.0	V
Output Capacitance	C_{obo}	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$	–	–	150	pF
Small–Signal Forward Current Transfer Ratio	$ h_{fe} $	$V_{CE} = 10\text{V}$, $I_C = 200\text{mA}$, $f = 1\text{MHz}$	1	7	–	
Second Breakdown Collector Current	$I_{S/b}$	$V_{CE} = 50\text{V}$, with Base forward biased, Pulse duration (non–repetitive) = 1sec	0.9	–	–	A
Second Breakdown Energy	$E_{S/b}$	$V_{BE} = -4\text{V}$, $I_C = 3\text{A}$, with Base reverse biased, $R_B = 50\Omega$, $L = 100\mu\text{H}$	0.45	–	–	mJ
Delay Time	t_d	$V_{CC} = 250\text{V}$, $I_{B1} = I_{B2} = 200\text{mA}$, $I_C = 1.2\text{A}$	–	0.02	–	μs
Rise Time	t_r		–	0.3	0.75	μs
Storage Time	t_s		–	2.8	5.0	μs
Fall Time	t_f		–	0.3	0.75	μs

Note 1. Pulsed: Pulse Duration $\leq 350\mu\text{s}$, Duty Factor = 2%.

